

LS5018 P-CHANNEL JFET



Linear Systems replaces discontinued Siliconix 2N5018 The LS5018 is a single P-Channel JFET switch

This p-channel analog switch is designed to provide low on-resistance and fast switching.

The SOT-23 package provides ease of manufacturing, and a lower cost assembly option.

(See Packaging Information).

LS5018 Benefits:

- Low Insertion Loss
- No offset or error voltage generated by closed switch
- Purely resistive

LS5018 Applications:

- **Analog Switches**
- Commutators
- Choppers

FEATURES					
DIRECT REPLACEMENT FOR SILICONIX 2N5018					
ZERO OFFSET VOLTAGE					
LOW ON RESISTANCE	$r_{DS(on)} \le 75\Omega$				
ABSOLUTE MAXIMUM RATINGS					
@ 25°C (unless otherwise noted)					
Maximum Temperatures					
Storage Temperature	-55°C to +200°C				
Operating Junction Temperature	-55°C to +200°C				
Maximum Power Dissipation					
Continuous Power Dissipation	500mW				
MAXIMUM CURRENT					
Gate Current (Note 1)	I _G = -50mA				
MAXIMUM VOLTAGES					
Gate to Drain Voltage	V _{GDS} = 30V				
Gate to Source Voltage	V _{GSS} = 30V				

LS5018 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
BV_GSS	Gate to Source Breakdown Voltage	30				$I_G = 1\mu A$, $V_{DS} = 0V$
$V_{GS(off)}$	Gate to Source Cutoff Voltage	1		10	V	$V_{DS} = -15V$, $I_{D} = -1\mu A$
$V_{DS(on)}$	Drain to Source On Voltage	-		-0.5		$V_{GS} = 0V$, $I_D = -6mA$
I _{DSS}	Drain to Source Saturation Current (Note 2)	-10			mA	$V_{DS} = -20V, V_{GS} = 0V$
I _{GSS}	Gate Reverse Current	-		2	_nA	$V_{GS} = 15V, \ V_{DS} = 0V$
I _{D(off)}	Drain Cutoff Current			-10		$V_{DS} = -15V, V_{GS} = 12V$
	' 4 0 7	-		-1 0	μA	$V_{DS} = -15V, V_{GS} = 7V$
I _{DGO}	D <mark>ra</mark> in Re <mark>v</mark> erse Current			-2	nA	$V_{DG} = -15V, I_{S} = 0A$
r _{DS(on)}	Drain to Source On Resistance			75	Ω	$I_D = -1 \text{mA}, V_{GS} = 0 \text{V}$

LS5018 DYNAMIC ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
r _{DS(on)}	Drain to Source On Resistance	-		75	Ω	$I_D = 0A$, $V_{GS} = 0V$, $f = 1kHz$
C_{iss}	Input Capacitance	-		45	pF	$V_{DS} = -15V$, $V_{GS} = 0V$, $f = 1MHz$
C_{rss}	Reverse Transfer Capacitance			10		$V_{DS} = 0V, V_{GS} = 12V, f = 1MHz$

LS5018 SWITCHING CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC		UNITS	CONDITIONS	
t _{d(on)}	Turn On Time	15	- ns		V _{GS} (L) = 12V
t _r	Turn On Rise Time	20		$V_{GS}(H) = 0V$	
t _{d(off)}	Turn Off Time	15		115	See Switching Circuit
t _f	Turn Off Fall Time	50		· ·	

Note 1 - Absolute maximum ratings are limiting values above which LS5018 serviceability may be impaired.

LS5018 SWITCHING CIRCUIT PARAMETERS

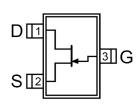
V _{DD}	-6V
V _{GG}	12V
R _L	910Ω
R_G	220Ω
I _{D(on)}	-6mA

Micross Components Europe

Available Packages:

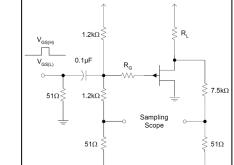
LS5018 in SOT-23 LS5018 in bare die.

Please contact Micross for full package and die dimensions



SOT-23 (Top View)

SWITCHING TEST CIRCUIT







Tel: +44 1603 788967

Email: chipcomponents@micross.com Web: http://www.micross.com/distribution

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Note 2 – Pulse test: PW≤ 300 us. Duty Cycle ≤ 3%